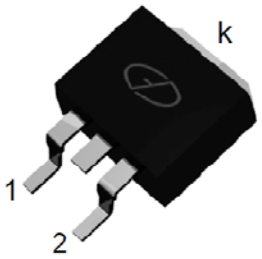
MBRB20150CT

Schottky Barrier Rectifier

Reverse Voltage 150 Volts Forward Current 20 Amperes

Features

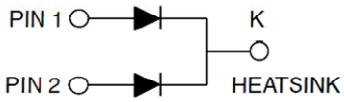
- Plastic package has underwriters Laboratory Flammability Classification 94V-0
- Dual rectifier construction, positive center tap
- Metal of silicon rectifier, majority carrier conduction
- Low forward voltage, high efficiency
- Guarding for over voltage protection



Package: TO-263

Mechanical Data

- Case: Epoxy, Molded
- Weight: 1.4grams（approximately）
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 sec
- Shipped 50 units per plastic tube or tape reel packing 800/reel



Maximum Ratings & Electrical Characteristics

(T_A=25℃ unless otherwise noted)

PARAMETER	TEST CONDITIONS		SYMBOL	MBRB20150CT	UNIT
Maximum repetitive peak reverse voltage			V_{RRM}	150	V
Working peak reverse voltage			V_{RWM}	150	V
Maximum DC blocking voltage			V_{DC}	150	V
Maximum average forward rectified current at T_C=105°C total device per diode			I_F(AV)	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode			I_{FSM}	150	A
Peak repetitive reverse current per leg at t_p=2.0us ,1KHz			I_{RRM}	1.0	A
Voltage rate of change（rated V_R）			$D_{V/dt}$	10000	V/us
Operating junction temperature range			T_J	—55 to+150	°C
Storage temperature range			T_{STG}	—55 to+150	°C
Maximum instantaneous forward voltage per leg	I_F=10A I_F=10A	T_C=25℃ T_C=125℃	V_F	0.92 0.82	V
Maximum reverse current per leg at working peak Reverse voltage		T_J=25℃ T_J=100°C	I_R	200 15	uA mA

Thermal Characteristics T_A=25℃ unless otherwise noted

Symbol	Parameter	TYP（TO-263）	Unit
RθJC	Thermal Resistance, Junction to Case per Leg	2.0	°C /W
RθJA	Thermal Resistance, Junction to Ambient per Leg	62.5	°C /W

Note： Pulse test:300us pulse width, duty cycle=2%

Ratings and Characteristics Curves

(T_A = 25℃ unless otherwise noted)

Fig. 1: Average forward power dissipation versus average forward current (per diode).

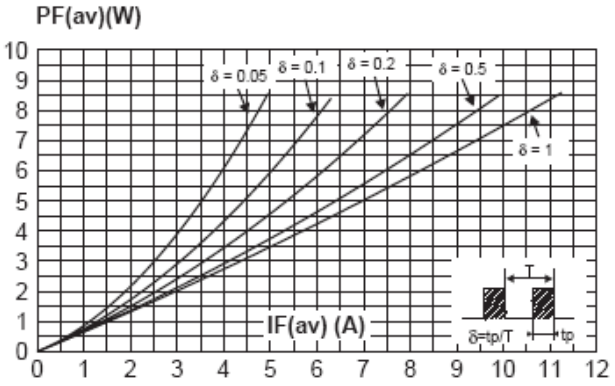


Fig. 2: Average forward current versus ambient temperature (δ = 0.5, per diode).

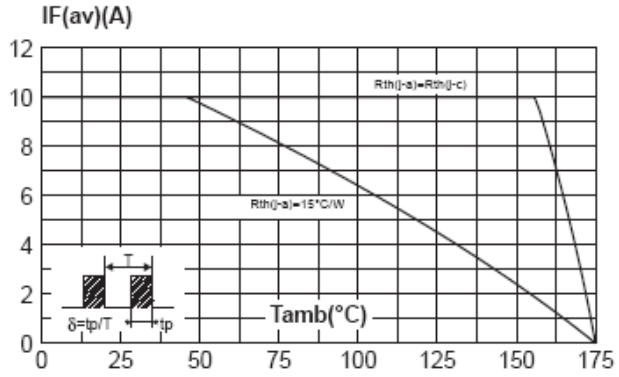


Fig. 3: Non repetitive surge peak forward current versus overload duration (maximum values, per diode).

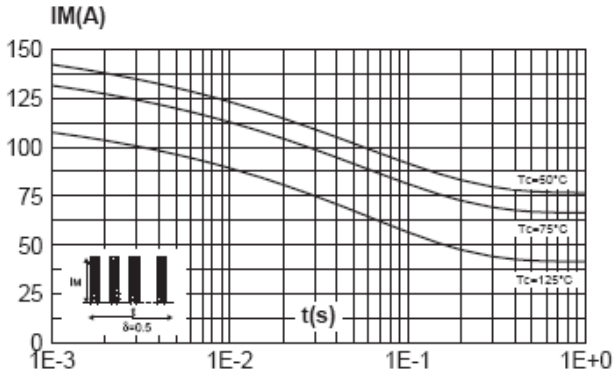


Fig. 4: Relative variation of thermal impedance junction to case versus pulse duration (per diode).

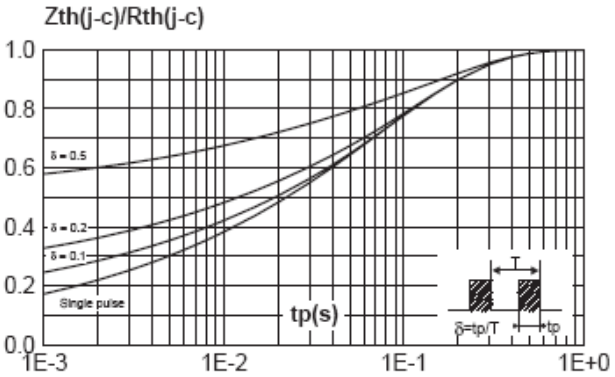


Fig. 5: Reverse leakage current versus reverse voltage applied (typical values, per diode).

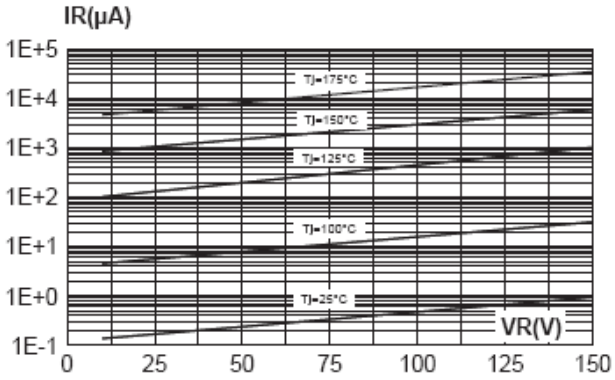
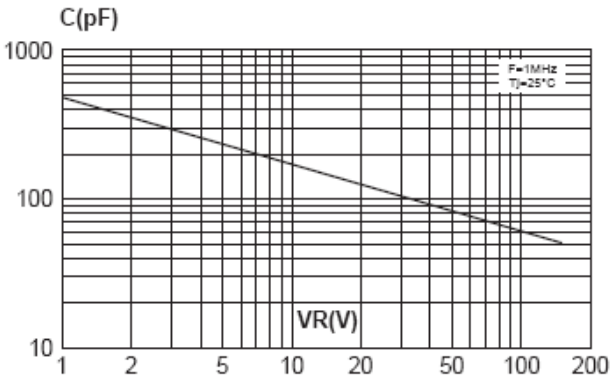


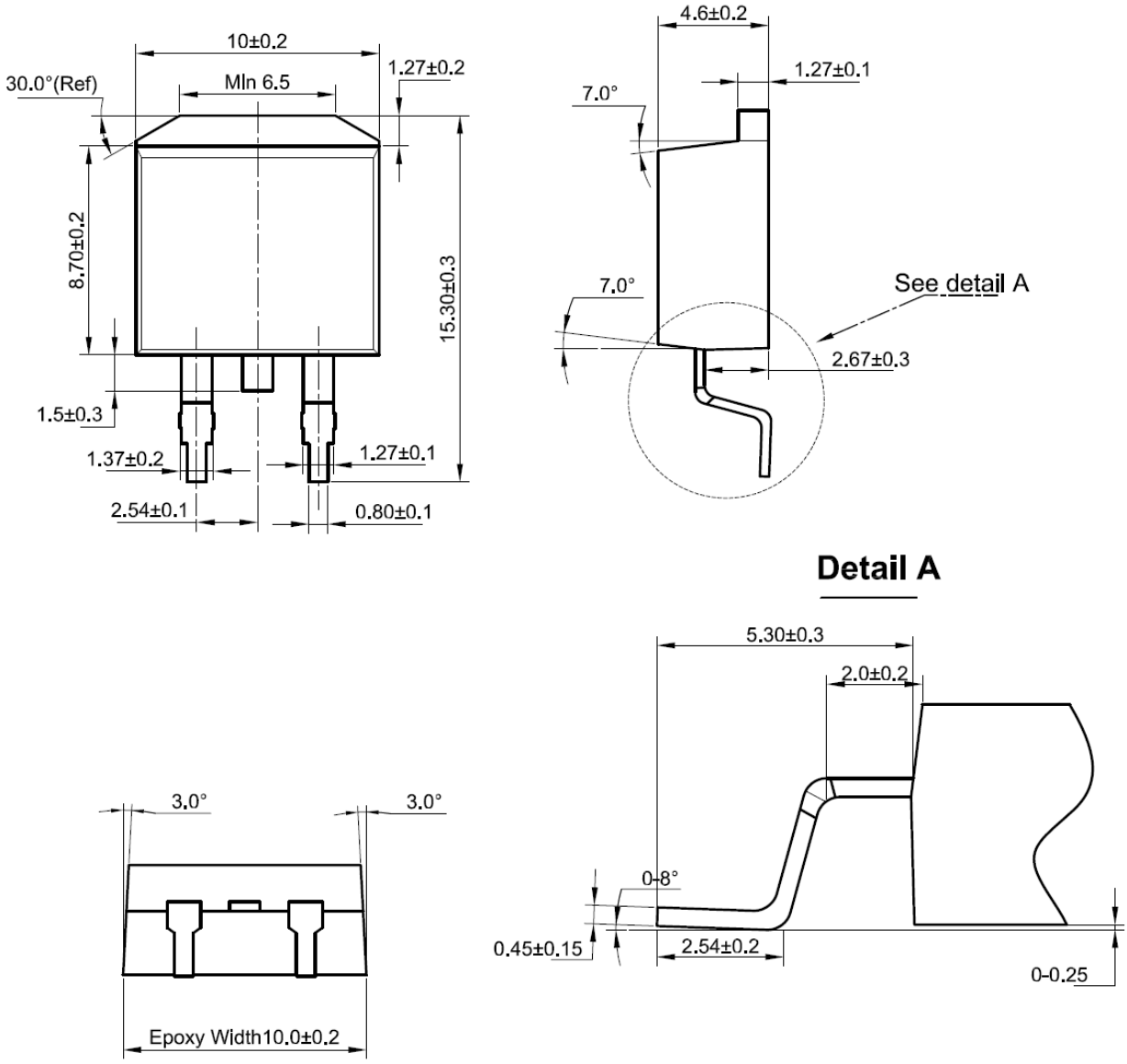
Fig. 6: Junction capacitance versus reverse voltage applied (typical values, per diode).



Package Outline Dimensions

Unit: millimeters

TO-263



Disclaimers

These materials are intended as a reference to assist our customers in the selection of the Suzhou Goo-Ark product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Suzhou Good-Ark Electronics Co., Ltd.or a third party.

Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Suzhou Good-Ark Electronics Co., Ltd. without notice due to product improvements or other reasons. It is therefore recommended that customers contact Suzhou Good-Ark Electronics Co., Ltd. or an authorized Suzhou Good-Ark Electronics Co., Ltd. for the latest product information before purchasing a product listed herein. The information described here may contain technical inaccuracies or typographical errors. Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors. Please also pay attention to information published by Suzhou Good-Ark Electronics Co., Ltd. by various means, including our website home page.
(http://www.goodark.com)

When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, Please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Suzhou Good-Ark Electronics Co., Ltd. assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.

The prior written approval of Suzhou Good-Ark Electronics Co., Ltd. is necessary to reprint or reproduce in whole or in part these materials.

Please contact Suzhou Good-Ark Electronics Co., Ltd. or an authorized distributor for further details on these materials or the products contained herein.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers ***category:***

Click to view products by Good-Ark ***manufacturer:***

Other Similar products are found below :

CUS06(TE85L,Q,M) MA4E2039 D1FH3-5063 MBR0530L-TP MBR10100CT-BP MBR30H100MFST1G MMBD301M3T5G PMAD1103-LF PMAD1108-LF RB160M-50TR RB520S-30 RB551V-30 DD350N18K DZ435N40K DZ600N16K BAS16E6433HTMA1 BAS 3010S-02LRH E6327 BAT 54-02LRH E6327 IDL02G65C5XUMA1 NSR05F40QNXT5G NSVR05F40NXT5G JANS1N6640 SB07-03C-TB-H SB1003M3-TL-W SBAT54CWT1G SBM30-03-TR-E SBS818-TL-E SK32A-LTP SK33A-TP SK34A-TP SK34B-TP SMD1200PL-TP ACDBN160-HF SS3003CH-TL-E STPS30S45CW PDS3100Q-7 GA01SHT18 CRS10I30A(TE85L,QM MBR1240MFST1G MBRB30H30CT-1G BAS28E6433HTMA1 BAS 70-02L E6327 HSB123JTR-E JANTX1N5712-1 VS-STPS40L45CW-N3 DD350N12K SB007-03C-TB-E SB10015M-TL-E SB1003M3-TL-E SK110-LTP